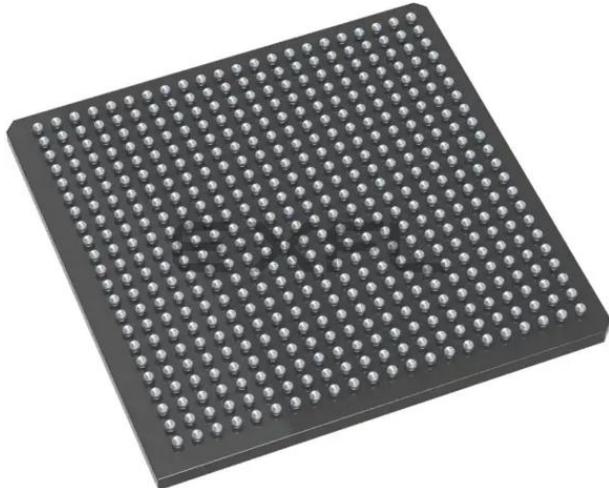


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### [\*\*Embedded - System On Chip \(SoC\): The Heart of Modern Embedded Systems\*\*](#)

**Embedded - System On Chip (SoC)** refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

### **What are [Embedded - System On Chip \(SoC\)](#)?**

**System On Chip (SoC)** integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

#### **Details**

Product Status	Active
Architecture	MCU, FPGA
Core Processor	ARM® Cortex®-M3
Flash Size	256KB
RAM Size	64KB
Peripherals	DDR, PCIe, SERDES
Connectivity	CANbus, Ethernet, I²C, SPI, UART/USART, USB
Speed	166MHz
Primary Attributes	FPGA - 25K Logic Modules
Operating Temperature	-40°C ~ 125°C (TJ)
Package / Case	484-BGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/microchip-technology/m2s025ts-1fgg484t2">https://www.e-xfl.com/product-detail/microchip-technology/m2s025ts-1fgg484t2</a>

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**Table 7 • Package Thermal Resistance**

Product M2GL/M2S	$\theta_{JA}$			$\theta_{JB}$	$\theta_{JC}$	Units
	Still Air	1.0 m/s	2.5 m/s			
<b>005</b>						
FGG484	19.36	15.81	14.63	9.74	5.27	°C/W
VFG256	41.30	38.16	35.30	28.41	3.94	°C/W
VFG400	20.19	16.94	15.41	8.86	4.95	°C/W
<b>010</b>						
FGG484	18.22	14.83	13.62	8.83	4.92	°C/W
VFG256	37.36	34.26	31.45	24.84	7.89	°C/W
VFG400	19.40	15.75	14.22	8.11	4.22	°C/W
<b>025</b>						
FGG484	17.03	13.66	12.45	7.66	4.18	°C/W
VFG256	33.85	30.59	27.85	21.63	6.13	°C/W
VFG400	18.36	14.89	13.36	7.12	3.41	°C/W
<b>060</b>						
FGG484	15.40	12.06	10.85	6.14	3.15	°C/W
VFG400	17.45	14.01	12.47	6.22	2.69	°C/W
FGG676	15.49	12.21	11.06	7.07	3.87	°C/W
<b>090</b>						
FGG484	14.64	11.37	10.16	5.43	2.77	°C/W
FGG676	14.52	11.19	10.37	6.17	3.24	°C/W

### 4.3.2 Theta-JA

Junction-to-ambient thermal resistance ( $\theta_{JA}$ ) is determined under standard conditions specified by JEDEC (JESD-51), but it has little relevance in actual performance of the product. It should be used with caution, but it is useful for comparing the thermal performance of one package to another.

The maximum power dissipation allowed is calculated using EQ 4.

$$\text{Maximum Power Allowed} = \frac{T_{J(MAX)} - T_{A(MAX)}}{\theta_{JA}} \quad \text{EQ 4}$$

The absolute maximum junction temperature is 125°C. EQ 5 shows a sample calculation of the absolute maximum power dissipation allowed for the M2GL060TS-1FGG484 package at Automotive Grade 2 temperature and in still air, where:

$$\theta_{JA} = 15.4^{\circ}\text{C/W} \text{ (taken from Table 7 on page 6).}$$

$$T_A = 105^{\circ}\text{C}$$

$$\text{Maximum Power Allowed} = \frac{125^{\circ}\text{C} - 105^{\circ}\text{C}}{15.4^{\circ}\text{C/W}} = 1.3 \text{ W} \quad \text{EQ 5}$$

The power consumption of a device can be calculated using the Microsemi SoC Products Group power calculator. The device's power consumption must be lower than the calculated maximum power dissipation by the package.

**Table 30 • LVCMS 2.5 V Transmitter Drive Strength Specifications**

Output Drive Selection			VOH (V) Min	VOL (V) Max	IOH (at VOH) mA	IOL (at VOL) mA
MSIO I/O Bank	MSIOD I/O Bank	DDRIO I/O Bank (With Software Default Fixed Code)				
2 mA	2 mA	2 mA	1.7	0.7	2	2
4 mA	4 mA	4 mA	1.7	0.7	4	4
6 mA	6 mA	6 mA	1.7	0.7	6	6
8 mA	8 mA	8 mA	1.7	0.7	8	8
12 mA	12 mA	12 mA	1.7	0.7	12	12
16 mA	N/A	16 mA	1.7	0.7	16	16

*Note:* For board design considerations, output slew rates extraction, detailed output buffer resistances and I/V Curve use the corresponding IBIS models located at:  
<http://www.microsemi.com/products/fpga-soc/design-resources/ibis-models>.

### 8.6.3.2 AC Switching Characteristics

#### AC Switching Characteristics for Receiver (Input Buffers)

**Table 31 • LVCMS 2.5 V AC Switching Characteristics for Receiver (Input Buffers)**Worst-case Automotive Grade 2 Conditions:  $T_J = 125^\circ\text{C}$ ,  $VDD = 1.14 \text{ V}$ ,  $VDDI = 2.375 \text{ V}$ 

On-Die Termination (ODT) in $\Omega$	Speed Grade -1		Units
	$t_{PY}$	$t_{PYS}$	
LVCMS 2.5 V (for DDRIO I/O Bank)	None	1.903	ns
LVCMS 2.5 V (for MSIO I/O Bank)	None	2.689	ns
LVCMS 2.5 V (for MSIOD I/O Bank)	None	2.447	ns

#### AC Switching Characteristics for Transmitter (Output and Tristate Buffers)

**Table 32 • LVCMS 2.5 V AC Switching Characteristics for Transmitter (Output and Tristate Buffers)**Worst-case Automotive Grade 2 Conditions:  $T_J = 125^\circ\text{C}$ ,  $VDD = 1.14 \text{ V}$ ,  $VDDI = 2.375 \text{ V}$ 

Output Drive Selection	Slew Control	Speed Grade -1					Units
		$t_{DP}$	$t_{ZL}$	$t_{ZH}$	$t_{HZ}$	$t_{LZ}$	
<b>LVCMS 2.5 V (for DDRIO I/O Bank with Fixed Code)</b>							
2 mA	slow	3.967	3.664	3.986	4.172	3.811	ns
	medium	3.625	3.38	3.647	3.882	3.458	ns
	medium_fast	3.485	3.259	3.507	3.747	3.327	ns
	fast	3.458	3.253	3.48	3.74	3.31	ns
4 mA	slow	3.371	2.942	3.362	5.148	4.71	ns
	medium	3.063	2.701	3.059	4.874	4.381	ns
	medium_fast	2.925	2.566	2.92	4.686	4.248	ns
	fast	2.91	2.559	2.905	4.683	4.238	ns

**Table 41 • LVC MOS 1.5 V Maximum AC Switching Speeds**

Symbols	Parameters	Conditions	Min	Typ	Max	Units
<b>LVC MOS 1.5 V Maximum AC Switching Speed</b>						
Dmax	Maximum data rate (for DDRIO I/O Bank)	AC loading: 17 pF load, maximum drive/slew	–	–	210	Mbps
Dmax	Maximum data rate (for MSIO I/O Bank)	AC loading: 17 pF load, maximum drive/slew	–	–	140	Mbps
Dmax	Maximum data rate (for MSIOD I/O Bank)	AC loading: 17 pF load, maximum drive/slew	–	–	190	Mbps

**Table 42 • LVC MOS 1.5 V AC Test Parameters and Driver Impedance Specifications**

Symbols	Parameters	Min	Typ	Max	Units
<b>LVC MOS 1.5 V AC Calibrated Impedance Option</b>					
Rodt_cal	Supported output driver calibrated impedance (for DDRIO I/O Bank)	–	75, 60, 50, 40	–	Ω
<b>LVC MOS 1.5 V AC Test Parameters Specifications</b>					
Vtrip	Measuring/trip point for data path	–	0.75	–	V
Rent	Resistance for enable path ( $t_{ZH}$ , $t_{ZL}$ , $t_{HZ}$ , $t_{LZ}$ )	–	2k	–	Ω
Cent	Capacitive loading for enable path ( $t_{ZH}$ , $t_{ZL}$ , $t_{HZ}$ , $t_{LZ}$ )	–	5	–	pF
Cload	Capacitive loading for data path ( $t_{DP}$ )	–	5	–	pF

**Table 43 • LVC MOS 1.5 V Transmitter Drive Strength Specifications**

Output Drive Selection			VOH (V)	VOL (V)	IOH (at VOH) mA	IOL (at VOL) mA
MSIO I/O Bank	MSIOD I/O Bank	DDRIO I/O Bank (with Fixed Code)	Min	Max		
2 mA	2 mA	2 mA	$VDDI \times 0.75$	$VDDI \times 0.25$	2	2
4 mA	4 mA	4 mA	$VDDI \times 0.75$	$VDDI \times 0.25$	4	4
6 mA	6 mA	6 mA	$VDDI \times 0.75$	$VDDI \times 0.25$	6	6
8 mA	N/A	8 mA	$VDDI \times 0.75$	$VDDI \times 0.25$	8	8
N/A	N/A	10 mA	$VDDI \times 0.75$	$VDDI \times 0.25$	10	10
N/A	N/A	12 mA	$VDDI \times 0.75$	$VDDI \times 0.25$	12	12

**Table 53 • PCI/PCI-X AC Specifications (Applicable to MSIO Bank Only)**

Symbols	Parameters	Conditions	Min	Typ	Max	Units
<b>PCI/PCI-X AC Specifications</b>						
Dmax	Maximum data rate (MSIO I/O Bank)	AC Loading: per JEDEC specifications	–	–	560	Mbps
<b>PCI/PCI-X AC Test Parameters Specifications</b>						
Vtrip	Measuring/trip point for data path (falling edge)	–	0.615 × VDDI	–	V	
Vtrip	Measuring/trip point for data path (rising edge)	–	0.285 × VDDI	–	V	
Rtt_test	Resistance for data test path	–	25	–	Ω	
Rent	Resistance for enable path ( $t_{ZH}$ , $t_{ZL}$ , $t_{HZ}$ , $t_{LZ}$ )	–	2k	–	Ω	
Cent	Capacitive loading for enable path ( $t_{ZH}$ , $t_{ZL}$ , $t_{HZ}$ , $t_{LZ}$ )	–	5	–	pF	
Cload	Capacitive loading for data path ( $t_{DP}$ )	–	10	–	pF	

### 8.6.7.2 AC Switching Characteristics

#### AC Switching Characteristics for Receiver (Input Buffers)

**Table 54 • PCI/PCIX AC Switching Characteristics for Receiver (Input Buffers)**Worst-Case Automotive Grade 2 Conditions:  $T_J = 125^\circ\text{C}$ ,  $\text{VDD} = 1.14 \text{ V}$ ,  $\text{VDDI} = 3.15 \text{ V}$ 

ODT (On Die Termination) in Ω	Speed Grade –1		Units	
	$t_{PY}$	$t_{PYS}$		
PCI/PCIX (for MSIO I/O Bank)	None	2.379	2.387	ns

#### AC Switching Characteristics for Transmitter (Output and Tristate Buffers)

**Table 55 • PCI/PCIX AC Switching Characteristics for Transmitter (Output and Tristate Buffers)**Worst-Case Automotive Grade 2 Conditions:  $T_J = 125^\circ\text{C}$ ,  $\text{VDD} = 1.14 \text{ V}$ ,  $\text{VDDI}= 3.15 \text{ V}$ 

	Speed Grade –1					Units
	$t_{DP}$	$t_{ZL}$	$t_{ZH}$	$t_{HZ}$	$t_{LZ}$	
PCI/PCIX (for MSIO I/O Bank)	2.394	2.274	2.316	6.876	6.242	ns

## 8.7. Memory Interface and Voltage Referenced I/O Standards

### 8.7.1 High-Speed Transceiver Logic (HSTL)

The High-Speed Transceiver Logic (HSTL) standard is a general purpose high-speed bus standard sponsored by IBM (EIA/JESD8-6). IGLOO2 FPGA and SmartFusion2 SoC FPGA devices support two classes of the 1.5 V HSTL. These differential versions of the standard require a differential amplifier input buffer and a push-pull output buffer.

#### 8.7.1.1 Minimum and Maximum Input and Output Levels Specification

**Table 56 • HSTL DC Voltage Specification (Applicable to DDRIO I/O Bank Only)**

Symbols	Parameters	Conditions	Min	Typ	Max	Units
<b>HSTL Recommended DC Operating Conditions</b>						
VDDI	Supply voltage		1.425	1.5	1.575	V
VTT	Termination voltage		0.698	0.750	0.803	V
VREF	Input reference voltage		0.698	0.750	0.803	V
<b>HSTL DC Input Voltage Specification</b>						
VIH (DC)	DC input logic High	VREF + 0.1	–	1.575	–	V
VIL (DC)	DC input logic Low	–0.3	–	VREF – 0.1	–	V
IIH (DC)	Input current High	–	–	10	–	µA
IIL (DC)	Input current Low	–	–	10	–	µA
<b>HSTL DC Output Voltage Specification</b>						
<b>HSTL Class I</b>						
VOH	DC output logic High	VDDI – 0.4	–	–	–	V
VOL	DC output logic Low	–	–	0.4	–	V
IOH at VOH	Output minimum source DC current	–7.0	–	–	–	mA
IOL at VOL	Output minimum sink current	7.0	–	–	–	mA
<b>HSTL Class II</b>						
VOH	DC output logic High	VDDI – 0.4	–	–	–	V
VOL	DC output logic Low	–	–	0.4	–	V
IOH at VOH	Output minimum source DC current	–15.0	–	–	–	mA
IOL at VOL	Output minimum sink current	15.0	–	–	–	mA
<b>HSTL DC Differential Voltage Specifications</b>						
VID (DC)	DC input differential voltage	0.2	–	–	–	V

### 8.7.4 Stub-Series Terminated Logic 1.8 V (SSTL18)

SSTL18 Class I and Class II are supported in IGLOO2 and SmartFusion2 SoC FPGAs, and also comply with the reduced and full drive double date rate (DDR2) standard. IGLOO2 and SmartFusion2 SoC FPGA I/Os support both standards for single-ended signaling and differential signaling for SSTL18. This standard requires a differential amplifier input buffer and a push-pull output buffer.

#### 8.7.4.1 Minimum and Maximum Input and Output Levels Specification

Table 64 • DDR2/SSTL18 AC/DC Minimum and Maximum Input and Output Levels Specification

Symbols	Parameters	Min	Typ	Max	Units	Notes
<b>Recommended DC Operating Conditions</b>						
VDDI	Supply voltage	1.71	1.8	1.89	V	–
VTT	Termination voltage	0.838	0.900	0.964	V	–
VREF	Input reference voltage	0.838	0.900	0.964	V	–
<b>SSTL18 DC Input Voltage Specification</b>						
VIH (DC)	DC input logic High	VREF + 0.125	–	1.89	V	–
VIL (DC)	DC input logic Low	–0.3	–	VREF – 0.125	V	–
IIH (DC)	Input current High	–	–	10	µA	–
IIL (DC)	Input current Low	–	–	10	µA	–
<b>SSTL18 DC Output Voltage Specification</b>						
<b>SSTL18 Class I (DDR2 Reduced Drive)</b>						
VOH	DC output logic High	VTT + 0.603	–	–	V	–
VOL	DC output logic Low	–	–	VTT – 0.603	V	–
IOH at VOH	Output minimum source DC current (DDRIO I/O Bank only)	6.0	–	–	mA	–
IOL at VOL	Output minimum sink current (DDRIO I/O Bank only)	–6.0	–	–	mA	–
<b>SSTL18 Class II (DDR2 Full Drive)</b>						
VOH	DC output logic High	VTT + 0.603	–	–	V	–
VOL	DC output logic Low	–	–	VTT – 0.603	V	–
IOH at VOH	Output minimum source DC current (DDRIO I/O Bank only)	12.0	–	–	mA	–
IOL at VOL	Output minimum sink current (DDRIO I/O Bank only)	–12.0	–	–	mA	–
<b>SSTL18 DC Differential Voltage Specification</b>						
VID (DC)	DC input differential voltage	0.3	–	–	V	–
Note: *To meet JEDEC Electrical Compliance, use DDR2 Full Drive Transmitter.						

**Table 94 • M-LVDS AC Specifications**

Symbols	Parameters	Conditions	Min	Typ	Max	Units
<b>M-LVDS Maximum AC Switching Speeds</b>						
Dmax	Maximum data rate (for MSIO I/O Bank)	AC loading: 2 pF / 100 Ω differential load	–	–	450	Mbps
<b>M-LVDS Impedance Specification</b>						
Rt	Termination resistance	–	–	50	–	Ω
<b>M-LVDS AC Test Parameters Specifications</b>						
VTrip	Measuring/trip point for data path	–	Cross point	–	V	
Rent	Resistance for enable path (t <sub>ZH</sub> , t <sub>ZL</sub> , t <sub>HZ</sub> , t <sub>LZ</sub> )	–	2k	–	–	Ω
Cent	Capacitive loading for enable path (t <sub>ZH</sub> , t <sub>ZL</sub> , t <sub>HZ</sub> , t <sub>LZ</sub> )	–	5	–	–	pF

### 8.8.3.2 AC Switching Characteristics

#### AC Switching Characteristics for Receiver (Input Buffers)

**Table 95 • M-LVDS AC Switching Characteristics for Receiver (Input Buffers)**Worst-case Automotive Grade 2 conditions: T<sub>J</sub> = 125°C, VDD = 1.14 V, VDDI= 2.375 V

	On-Die Termination (ODT) in Ω	Speed Grade –1		Units
		t <sub>PD</sub>	t <sub>PY</sub>	
M-LVDS (for MSIO I/O Bank)	None	3.011	ns	
	100	3.006	ns	
M-LVDS (for MSIOD I/O Bank)	None	2.722	ns	
	100	2.725	ns	

#### AC Switching Characteristics for Transmitter (Output and Tristate Buffers)

**Table 96 • M-LVDS AC Switching Characteristics for Transmitter (Output and Tristate Buffers)**Worst-case Automotive Grade 2 conditions: T<sub>J</sub> = 125°C, VDD = 1.14 V, VDDI= 2.375 V

	Speed Grade –1					Units
	t <sub>DP</sub>	t <sub>ZL</sub>	t <sub>ZH</sub>	t <sub>HZ</sub>	t <sub>LZ</sub>	
M-LVDS (for MSIO I/O Bank)	2.78	2.632	2.616	2.447	2.436	ns

## 8.8.4 Mini-LVDS

Mini-LVDS is an unidirectional interface from the timing controller to the column drivers and is designed to the Texas Instruments Standard SLDA007A.

### 8.8.4.1 Mini-LVDS Minimum and Maximum Input and Output Levels

**Table 97 • Mini-LVDS DC Voltage Specification**

Symbols	Parameters	Conditions	Min	Typ	Max	Units
<b>Recommended DC Operating Conditions</b>						
VDDI	Supply voltage		2.375	2.5	2.625	V
<b>Mini-LVDS DC Input Voltage Specification</b>						
VI	DC Input voltage		0	–	2.925	V
<b>Mini-LVDS DC Output Voltage Specification</b>						
VOH	DC output logic High		1.25	1.425	1.6	V
VOL	DC output logic Low		0.9	1.075	1.25	V
<b>Mini-LVDS Differential Voltage Specification</b>						
VOD	Differential output voltage swing		300	–	600	mV
VOCM	Output common mode voltage		1	–	1.4	V
VICM	Input common mode voltage		0.3	–	1.2	V
VID	Input differential voltage		100	–	600	mV

**Table 98 • Mini-LVDS AC Specifications**

Symbols	Parameters	Conditions	Min	Typ	Max	Units
<b>Mini-LVDS Maximum AC Switching Speed</b>						
Dmax	Maximum data rate (MSIO I/O Bank)	AC loading: 2 pF / 100 Ω differential load	–	–	460	Mbps
Dmax	Maximum data rate (MSIOD I/O Bank)	AC loading: 10 pF / 100 Ω differential load	–	–	480	Mbps
<b>Mini-LVDS Impedance Specification</b>						
Rt	Termination resistance		–	100	–	Ω
<b>Mini-LVDS AC Test Parameters Specifications</b>						
VTrip	Measuring/trip point for data path		–	Cross point	–	V
Rent	Resistance for enable path ( $t_{ZH}$ , $t_{ZL}$ , $t_{HZ}$ , $t_{LZ}$ )		–	2k	–	Ω
Cent	Capacitive loading for enable path ( $t_{ZH}$ , $t_{ZL}$ , $t_{HZ}$ , $t_{LZ}$ )		–	5	–	pF

### 8.8.4.2. AC Switching Characteristics

#### AC Switching Characteristics for Receiver (Input Buffers)

**Table 99 • Mini-LVDS AC Switching Characteristics for Receiver (Input Buffers)**

Worst-case Automotive Grade 2 Conditions:  $T_J = 125^\circ\text{C}$ ,  $VDD = 1.14 \text{ V}$ ,  $VDDI = 2.375 \text{ V}$

	On-Die Termination (ODT) in $\Omega$	Speed Grade -1	Units
		$t_{PY}$	
Mini-LVDS (for MSIO I/O Bank)	None	3.112	ns
	100	2.995	ns
Mini-LVDS (for MSIOD I/O Bank)	None	2.612	ns
	100	2.612	ns

#### AC Switching Characteristics for Transmitter (Output and Tristate Buffers)

**Table 100 • Mini-LVDS AC Switching Characteristics for Transmitter (Output and Tristate Buffers)**

Worst-case Automotive Grade 2 Conditions:  $T_J = 125^\circ\text{C}$ ,  $VDD = 1.14 \text{ V}$ ,  $VDDI = 2.375 \text{ V}$

	Speed Grade -1					Units
	$t_{DP}$	$t_{ZL}$	$t_{ZH}$	$t_{HZ}$	$t_{LZ}$	
Mini-LVDS (for MSIO I/O Bank)	2.3	2.602	2.59	2.306	2.32	ns
<b>Mini-LVDS (for MSIOD I/O Bank)</b>						
No pre-emphasis	1.652	1.84	1.833	1.988	1.965	ns
Min pre-emphasis	1.652	1.84	1.833	1.988	1.965	ns
Med pre-emphasis	1.577	1.868	1.86	2.02	1.994	ns
Max pre-emphasis	1.555	1.894	1.883	2.048	2.019	ns

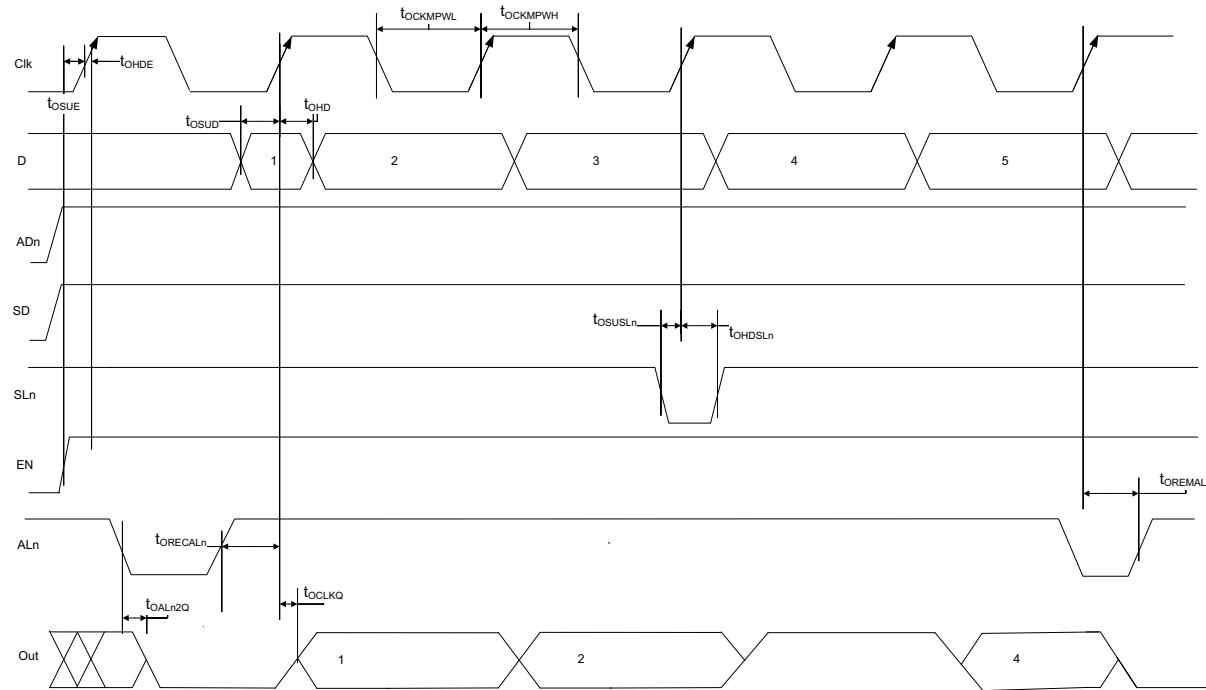
### 8.8.5 RSDS

Reduced Swing Differential Signaling (RSDS) is similar to an LVDS high-speed interface using differential signaling. RSDS has a similar implementation to LVDS devices and is only intended for point-to-point applications.

#### 8.8.5.1 Minimum and Maximum Input and Output Levels

**Table 101 • RSDS DC Voltage Specification**

Symbols	Parameters	Conditions	Min	Typ	Max	Units
<b>Recommended DC Operating Conditions</b>						
VDDI	Supply voltage		2.375	2.5	2.625	V
<b>RSDS DC Input Voltage Specification</b>						
VI	DC input voltage		0	-	2.925	V
<b>RSDS DC Output Voltage Specification</b>						
VOH	DC output logic High		1.25	1.425	1.6	V
VOL	DC output logic Low		0.9	1.075	1.25	V
<b>RSDS Differential Voltage Specification</b>						
VOD	Differential output voltage swing		100	-	600	mV
VOCM	Output common mode voltage		0.5	-	1.5	V

**Figure 8 • I/O Register Output Timing Diagram****Table 109 • Output/Enable Data Register Propagation Delays**  
Worst-Case Automotive Grade 2 Conditions:  $T_J = 125^\circ\text{C}$ ,  $VDD = 1.14 \text{ V}$ 

Parameter	Description	Measuring Nodes (from, to)*	Speed Grade -1	Units
$t_{OBYP}$	Bypass Delay of the Output/Enable Register	F,G or H,I	0.364	ns
$t_{OCLKQ}$	Clock-to-Q of the Output/Enable Register	E,G or E,I	0.272	ns
$t_{OSUD}$	Data Setup Time for the Output/Enable Register	A,E or J,E	0.196	ns
$t_{OHD}$	Data Hold Time for the Output/Enable Register	A,E or J,E	0	ns
$t_{OSUE}$	Enable Setup Time for the Output/Enable Register	B,E	0.433	ns
$t_{OHE}$	Enable Hold Time for the Output/Enable Register	B,E	0	ns
$t_{OSUSL}$	Synchronous Load Setup Time for the Output/Enable Register	D,E	0.203	ns
$t_{OHSL}$	Synchronous Load Hold Time for the Output/Enable Register	D,E	0	ns
$t_{OALn2Q}$	Asynchronous Clear-to-Q of the Output/Enable Register (ADn=1)	C,G or C,I	0.523	ns
	Asynchronous Preset-to-Q of the Output/Enable Register (ADn=0)	C,G or C,I	0.545	ns
$t_{OREMALn}$	Asynchronous Load Removal Time for the Output/Enable Register	C,E	0	ns
$t_{ORECALn}$	Asynchronous Load Recovery Time for the Output/Enable Register	C,E	0.035	ns

**Table 126 • uSRAM (RAM128x9) in 128x9 Mode**Worst-Case Automotive Grade 2 Conditions:  $T_J = 125^\circ\text{C}$ ,  $VDD = 1.14 \text{ V}$  (continued)

Parameter	Description	Speed Grade -1		Units
		Min	Max	
$t_{BLKSU}$	Read Block Select Setup Time	1.898	–	ns
$t_{BLKHD}$	Read Block Select Hold Time	-0.671	–	ns
$t_{BLK2Q}$	Read Block Select to Out Disable Time (when Pipe-Lined Registered is Disabled)	–	2.14	ns
$t_{RSTREM}$	Read Asynchronous Reset Removal Time (Pipelined Clock)	-0.15	–	ns
	Read Asynchronous Reset Removal Time (Non-Pipelined Clock)	0.047	–	ns
$t_{RSTREC}$	Read Asynchronous Reset Recovery Time (Pipelined Clock)	0.524	–	ns
	Read Asynchronous Reset Recovery Time (Non-Pipelined Clock)	0.244	–	ns
$t_{R2Q}$	Read Asynchronous Reset to Output Propagation Delay (with Pipe-Line Register Enabled)	–	0.865	ns
$t_{SRSTSU}$	Read Synchronous Reset Setup Time	0.279	–	ns
$t_{SRSTHD}$	Read Synchronous Reset Hold Time	0.062	–	ns
$t_{CCY}$	Write Clock Period	4	–	ns
$t_{CCLKMPWH}$	Write Clock Minimum Pulse Width High	1.8	–	ns
$t_{CCLKMPWL}$	Write Clock Minimum Pulse Width Low	1.8	–	ns
$t_{BLKCSU}$	Write Block Setup Time	0.417	–	ns
$t_{BLKCHD}$	Write Block Hold Time	0.007	–	ns
$t_{DINCSU}$	Write Input Data setup Time	0.104	–	ns
$t_{DINCHD}$	Write Input Data hold Time	0.142	–	ns
$t_{ADDRCSU}$	Write Address Setup Time	0.091	–	ns
$t_{ADDRCHD}$	Write Address Hold Time	0.24	–	ns
$t_{WECSU}$	Write Enable Setup Time	0.41	–	ns
$t_{WECHD}$	Write Enable Hold Time	-0.027	–	ns
Fmax	Maximum Frequency	–	250	MHz

**Table 128 • uSRAM (RAM256x4) in 256x4 Mode**Worst-Case Automotive Grade 2 Conditions:  $T_J = 125^\circ\text{C}$ ,  $VDD = 1.14 \text{ V}$  (continued)

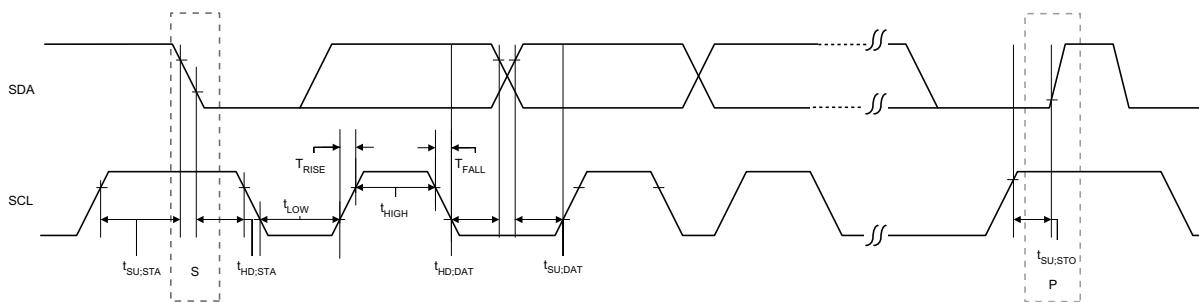
Parameter	Description	Speed Grade -1		Units
		Min	Max	
$t_{SRSTSU}$	Read Synchronous Reset Setup Time	0.279	—	ns
$t_{SRSTHD}$	Read Synchronous Reset Hold Time	0.062	—	ns
$t_{CCY}$	Write Clock Period	4	—	ns
$t_{CCLKMPWH}$	Write Clock Minimum Pulse Width High	1.8	—	ns
$t_{CCLKMPWL}$	Write Clock Minimum Pulse Width Low	1.8	—	ns
$t_{BLKCSU}$	Write Block Setup Time	0.417	—	ns
$t_{BLKCHD}$	Write Block Hold Time	0.007	—	ns
$t_{DINCSU}$	Write Input Data setup Time	0.104	—	ns
$t_{DINCHD}$	Write Input Data hold Time	0.142	—	ns
$t_{ADDRCSU}$	Write Address Setup Time	0.091	—	ns
$t_{ADDRCHD}$	Write Address Hold Time	0.253	—	ns
$t_{WECSU}$	Write Enable Setup Time	0.41	—	ns
$t_{WECHD}$	Write Enable Hold Time	-0.027	—	ns
Fmax	Maximum Frequency	—	250	MHz

**Table 129 • uSRAM (RAM512x2) in 512x2 Mode**Worst-Case Automotive Grade 2 Conditions:  $T_J = 125^\circ\text{C}$ ,  $VDD = 1.14 \text{ V}$ 

Parameter	Description	Speed Grade -1		Units
		Min	Max	
$t_{CY}$	Read Clock Period	4	—	ns
$t_{CLKMPWH}$	Read Clock Minimum Pulse Width High	1.8	—	ns
$t_{CLKMPWL}$	Read Clock Minimum pulse Width Low	1.8	—	ns
$t_{PLCY}$	Read Pipe-line clock period	4	—	ns
$t_{PLCLKMPWH}$	Read Pipe-line clock Minimum Pulse Width High	1.8	—	ns
$t_{PLCLKMPWL}$	Read Pipe-line clock Minimum Pulse Width Low	1.8	—	ns
$t_{CLK2Q}$	Read Access Time with Pipeline Register	—	0.276	ns
	Read Access Time without Pipeline Register	—	1.824	ns
$t_{ADDRSU}$	Read Address Setup Time in Synchronous Mode	0.311	—	ns
	Read Address Setup Time in Asynchronous Mode	2.023	—	ns
$t_{ADDRHD}$	Read Address Hold Time in Synchronous Mode	0.141	—	ns
	Read Address Hold Time in Asynchronous Mode	-0.599	—	ns
$t_{RDENSU}$	Read Enable Setup Time	0.287	—	ns
$t_{RDENHD}$	Read Enable Hold Time	0.059	—	ns
$t_{BLKSU}$	Read Block Select Setup Time	1.898	—	ns

**Table 130 • uSRAM (RAM1024x1) in 1024x1 Mode**Worst-Case Automotive Grade 2 Conditions:  $T_J = 125^\circ\text{C}$ ,  $VDD = 1.14 \text{ V}$  (continued)

Parameter	Description	Speed Grade -1		Units
		Min	Max	
$t_{CLK2Q}$	Read Access Time with Pipeline Register	—	0.274	ns
	Read Access Time without Pipeline Register	—	1.839	ns
$t_{ADDRSU}$	Read Address Setup Time in Synchronous Mode	0.311	—	ns
	Read Address Setup Time in Asynchronous Mode	2.041	—	ns
$t_{ADDRHD}$	Read Address Hold Time in Synchronous Mode	0.141	—	ns
	Read Address Hold Time in Asynchronous Mode	-0.623	—	ns
$t_{RDENSU}$	Read Enable Setup Time	0.287	—	ns
$t_{RDENHD}$	Read Enable Hold Time	0.059	—	ns
$t_{BLKSU}$	Read Block Select Setup Time	1.898	—	ns
$t_{BLKHD}$	Read Block Select Hold Time	-0.671	—	ns
$t_{BLK2Q}$	Read Block Select to Out Disable Time (when Pipe-Lined Registered is Disabled)	—	2.236	ns
$t_{RSTREM}$	Read Asynchronous Reset Removal Time (Pipelined Clock)	-0.15	—	ns
	Read Asynchronous Reset Removal Time (Non-Pipelined Clock)	0.047	—	ns
$t_{RSTREC}$	Read Asynchronous Reset Recovery Time (Pipelined Clock)	0.524	—	ns
	Read Asynchronous Reset Recovery Time (Non-Pipelined Clock)	0.244	—	ns
$t_{R2Q}$	Read Asynchronous Reset to Output Propagation Delay (With Pipe-Line Register Enabled)	—	0.862	ns
$t_{SRSTSU}$	Read Synchronous Reset Setup Time	0.279	—	ns
$t_{SRSTHD}$	Read Synchronous Reset Hold Time	0.062	—	ns
$t_{CCY}$	Write Clock Period	4	—	ns
$t_{CCLKMPWH}$	Write Clock Minimum Pulse Width High	1.8	—	ns
$t_{CCLKMPWL}$	Write Clock Minimum Pulse Width Low	1.8	—	ns
$t_{BLKCSU}$	Write Block Setup Time	0.417	—	ns
$t_{BLKCHD}$	Write Block Hold Time	0.007	—	ns
$t_{DINCSU}$	Write Input Data setup Time	0.003	—	ns
$t_{DINCHD}$	Write Input Data hold Time	0.142	—	ns
$t_{ADDRCSU}$	Write Address Setup Time	0.091	—	ns
$t_{ADDRCHD}$	Write Address Hold Time	0.255	—	ns
$t_{WECSU}$	Write Enable Setup Time	0.41	—	ns
$t_{WECHD}$	Write Enable Hold Time	-0.027	—	ns
Fmax	Maximum Frequency	—	250	MHz



**Figure 16 • I<sup>2</sup>C Timing Parameter Definition**

### 24.3 Serial Peripheral Interface (SPI) Characteristics

This section describes the DC and switching of the SPI interface. Unless otherwise noted, all output characteristics given are for a 35 pF load on the pins and all sequential timing characteristics are related to SPI\_x\_CLK. For timing parameter definitions, refer to Figure 17 on page 102.

**Table 159 • SPI Characteristics**

Worst-Case Automotive Grade 2 Conditions:  $T_J = 125^{\circ}\text{C}$ ,  $VDD = 1.14 \text{ V}$

Symbol	Description	All Devices/Speed Grades			Unit	Notes
		Min	Typ	Max		
sp1	<b>SPI_[0 1]_CLK minimum period</b>					
	SPI_[0 1]_CLK = PCLK/2	12	—	—	ns	—
	SPI_[0 1]_CLK = PCLK/4	24.1	—	—	ns	—
	SPI_[0 1]_CLK = PCLK/8	48.2	—	—	ns	—
	SPI_[0 1]_CLK = PCLK/16	0.1	—	—	μs	—
	SPI_[0 1]_CLK = PCLK/32	0.19	—	—	μs	—
	SPI_[0 1]_CLK = PCLK/64	0.39	—	—	μs	—
sp2	<b>SPI_[0 1]_CLK minimum pulse width high</b>					
	SPI_[0 1]_CLK = PCLK/2	6	—	—	ns	—
	SPI_[0 1]_CLK = PCLK/4	12.05	—	—	ns	—
	SPI_[0 1]_CLK = PCLK/8	24.1	—	—	ns	—
	SPI_[0 1]_CLK = PCLK/16	0.05	—	—	μs	—
	SPI_[0 1]_CLK = PCLK/32	0.095	—	—	μs	—
	SPI_[0 1]_CLK = PCLK/64	0.195	—	—	μs	—
	SPI_[0 1]_CLK = PCLK/128	0.385	—	—	μs	—
<i>Notes:</i>						
1. For specific Rise/Fall Times board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the Microsemi SoC Products Group website: <a href="http://www.microsemi.com/products/fpga-soc/design-resources/ibis-models">http://www.microsemi.com/products/fpga-soc/design-resources/ibis-models</a> .						
2. For allowable pclk configurations, refer to the Serial Peripheral Interface Controller section in the UG0331: SmartFusion2 Microcontroller Subsystem User Guide.						

**Table 163 • SPI Characteristics**Worst-Case Automotive Grade 2 Conditions:  $T_J = 125^\circ\text{C}$ ,  $VDD = 1.14 \text{ V}$  (continued)

Symbol	Description	All Devices/Speed Grades			Unit	Notes
		Min	Typ	Max		
sp3	<b>SPI_[0 1]_CLK minimum pulse width low</b>					
	SPI_[0 1]_CLK = PCLK/2	6	—	—	ns	—
	SPI_[0 1]_CLK = PCLK/4	12.05	—	—	ns	—
	SPI_[0 1]_CLK = PCLK/8	24.1	—	—	ns	—
	SPI_[0 1]_CLK = PCLK/16	0.05	—	—	μs	—
	SPI_[0 1]_CLK = PCLK/32	0.095	—	—	μs	—
	SPI_[0 1]_CLK = PCLK/64	0.195	—	—	μs	—
	SPI_[0 1]_CLK = PCLK/128	0.385	—	—	μs	—
sp4	SPI_[0 1]_CLK, SPI_[0 1]_DO, SPI_[0 1]_SS rise time (10%- 90%)	—	2.77	—	ns	1
sp5	SPI_[0 1]_CLK, SPI_[0 1]_DO, SPI_[0 1]_SS fall time (10%- 90%)	—	2.906	—	ns	1
<b>SPI Master Configuration</b>						
sp6m	SPI_[0 1]_DO setup time	(SPI_x_CLK_period/2) – 3.0	—	—	ns	2
sp7m	SPI_[0 1]_DO hold time	(SPI_x_CLK_period/2) – 2.5	—	—	ns	2
sp8m	SPI_[0 1]_DI setup time	8	—	—	ns	2
sp9m	SPI_[0 1]_DI hold time	2.5	—	—	ns	2
<b>SPI Slave Configuration</b>						
sp6s	SPI_[0 1]_DO setup time	(SPI_x_CLK_period/2) – 12.0	—	—	ns	2
sp7s	SPI_[0 1]_DO hold time	(SPI_x_CLK_period/2) + 3.0	—	—	ns	2
sp8s	SPI_[0 1]_DI setup time	2	—	—	ns	2
sp9s	SPI_[0 1]_DI hold time	3	—	—	ns	2
Notes:						
1. For specific Rise/Fall Times board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the Microsemi SoC Products Group website: <a href="http://www.microsemi.com/products/fpga-soc/design-resources/ibis-models">http://www.microsemi.com/products/fpga-soc/design-resources/ibis-models</a> .						
2. For allowable pclk configurations, refer to the Serial Peripheral Interface Controller section in the UG0331: SmartFusion2 Microcontroller Subsystem User Guide.						

# Datasheet Categories

## Categories

In order to provide the latest information to designers, some datasheet parameters are published before data has been fully characterized from silicon devices. The data provided for a given device, as highlighted in Table 1 on page 1 is designated as either "Product Brief," "Advance," "Preliminary," or "Production." The definitions of these categories are as follows:

### Product Brief

The product brief is a summarized version of a datasheet (advance or production) and contains general product information. This document gives an overview of specific device and family information.

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This label only applies to the DC and Switching Characteristics chapter of the datasheet and will only be used when the data has not been fully characterized.

### Preliminary

The datasheet contains information based on simulation and/or initial characterization. The information is believed to be correct, but changes are possible.

### Production

This version contains information that is considered to be final.

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